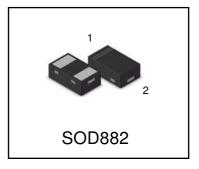


LESD8D24CT5G ESD PROTECTION DIODE

Discription

The LESD8D24CT5G is designed to protect voltage sensitive components from ESD. Excellent clamping capability, low leakage, and fast response time provide best in class protection on designs that are exposed to ESD. Because of its small size, it is suited for use in cellular phones, digital cameras and many other portable applications where board space is at a premium.







- Small Body Outline Dimensions: 1.00 mm x 0.60 mm
- Low Body Height: 0.50 mm
- Low Leakage
- Response Time is Typically < 1 ns
- ESD Rating of Class 3 per Human Body Model
- IEC61000-4-2 Level 4 ESD Protection
- S- Prefix for Automotive and Other Applications Requiring Unique Site and Control Change Requirements; AEC-Q101 Qualified and PPAP Capable.

Ordering information

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Device	Marking	Shipping	
LESD8D24CT5G S-LESD8D24CT5G	4C	10000/Tape&Reel	

-0 2

MAXIMUM RATINGS

Rating	Symbol	Value	Unit
IEC 61000-4-2 (ESD) Air Contact Contact discharge		±30 ±30	kV kV
Total Power Dissipation on FR-5 Board (Note 1) @ $T_A=25^{\circ}C$	PD	200	mW
Junction and Storage Temperature Range	TJ,TSTG	-55 to 150	°C
Lead Solder Temperature – Maximum (10 Second Duration)	TL	260	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Rating are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

1. FR-5 = 1.0*0.75*0.62 in.

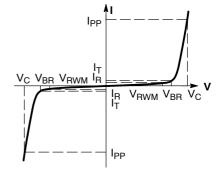


LESD8D24CT5G

Electrical Parameter

 $(T_A = 25^{\circ}C \text{ unless otherwise noted})$

Symbol	Parameter
I _{PP}	Maximum Reverse Peak Pulse Current
V _C	Clamping Voltage @ IPP
V _{RWM}	Working Peak Reverse Voltage
I _R	Maximum Reverse Leakage Current @ $V_{\mbox{RWM}}$
V _{BR}	Breakdown Voltage @ I _T
Ι _Τ	Test Current
P _{pk}	Peak Power Dissipation
С	Capacitance @ $V_R = 0$ and f = 1.0 MHz

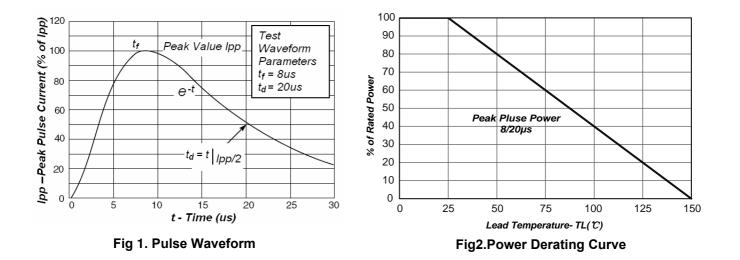


Electrical Parameter (T_A = 25°C unless otherwise noted)

Device	V _{RWM} (V)	I _R (μ Α) @ V _{RWM}	V _{BR (} V) * @ I _T = 1mA	I _{PP} (A)**	V _C (V) ** @ I _{PP} = 1A	V _C (V) ** @ I _{PP} = 5A	P _{PK} (W)**	C (pF) VR=0V, f=1MHz;
	Max	Max	Min	Max	Max	Max	Max	Max
LESD8D24CT5G	24	0.1	26	5	29	35	175	30

* V_{BR} is measured with a pulse test current I_T at an ambient temperature of 25°C.

** Surge current waveform per Figure 1.





LESD8D24CT5G

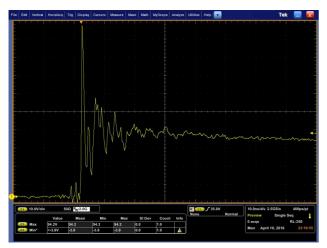


Figure 3.ESD Elamping Voltage Screenshot Positive 8 kV Eontact per IEE61000-4-2



Figure 4.ESD Elamping Voltage Screenshot Negative 8 kV Eontact per IEE61000-4-2

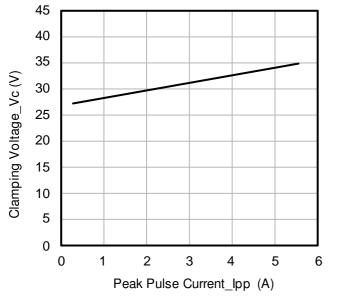
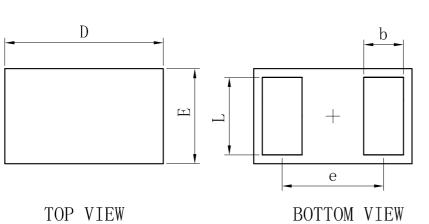


Fig 5 .Clamping Voltage vs. Peak Pulse Current

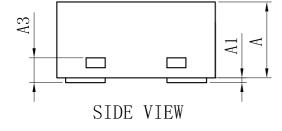
LESD8D24CT5G

OUTLINE AND DIMENSIONS

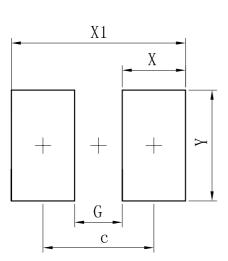
LRC



SOD882				
Dim	Min Typ		Max	
D	0.95	1.00	1.05	
Е	0.55	0.60	0.65	
е	-	0.64	Ι	
L	0.44	0.49	0.54	
b	0.20	0.25	0.30	
А	0.43	0.48	0.53	
A1	0	I	0.05	
A3	0.127REF.			
All Dimensions in mm				



SOLDERING FOOTPRINT



S0D882

SOD882

Dimensions	(mm)
С	0.70
G	0.30
Х	0.40
X1	1.10
Y	0.70